

Leakage Current Measurements from LHCb Vinícius Franco Lima 23/04/18





Silicon Detectors in LHCb

5m

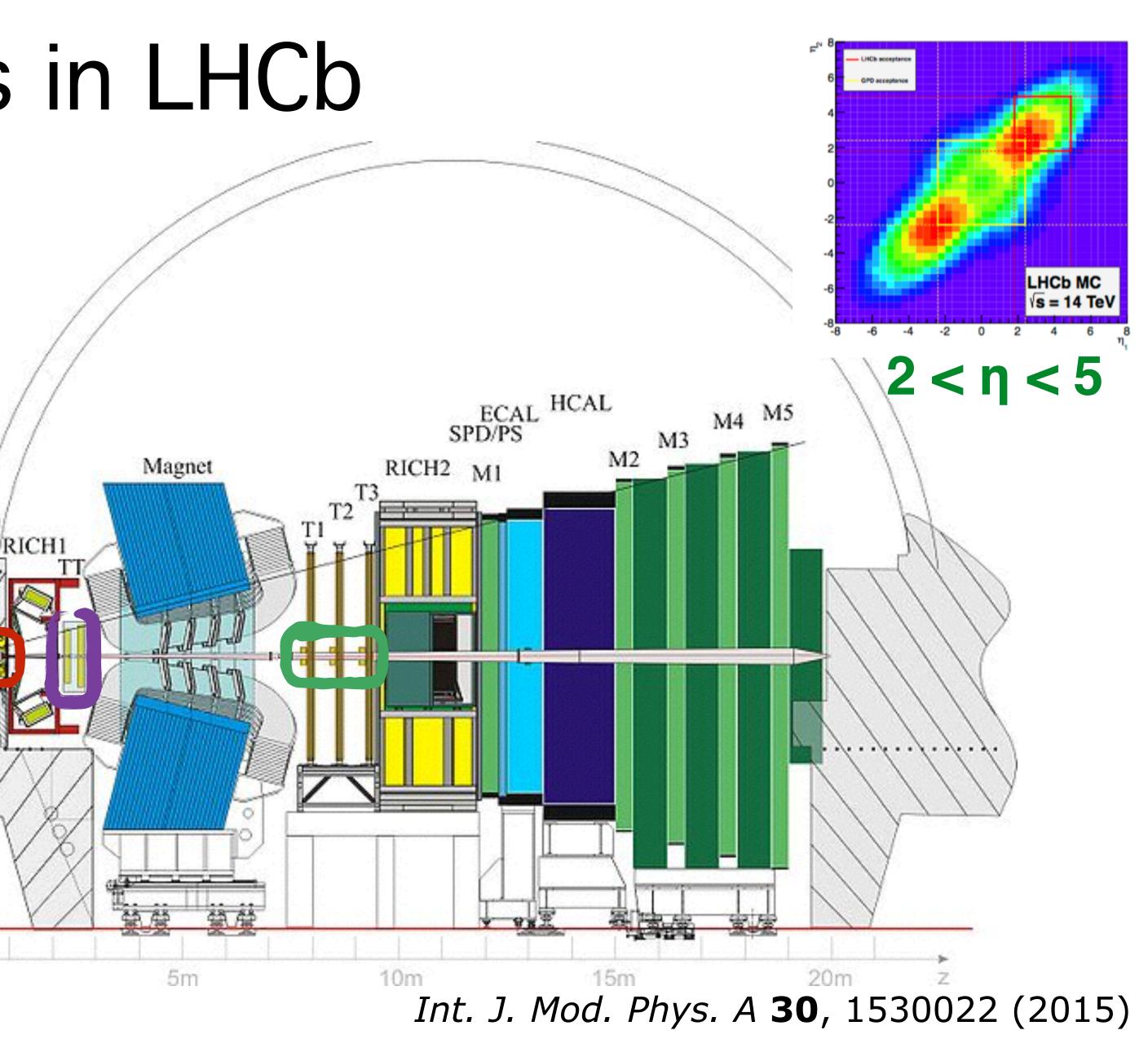
Vertex Locator (VELO)

Tracker Turicensis

Inner Tracker (||)









Silicon Detectors in LHCb

Vertex Locator (VELO)

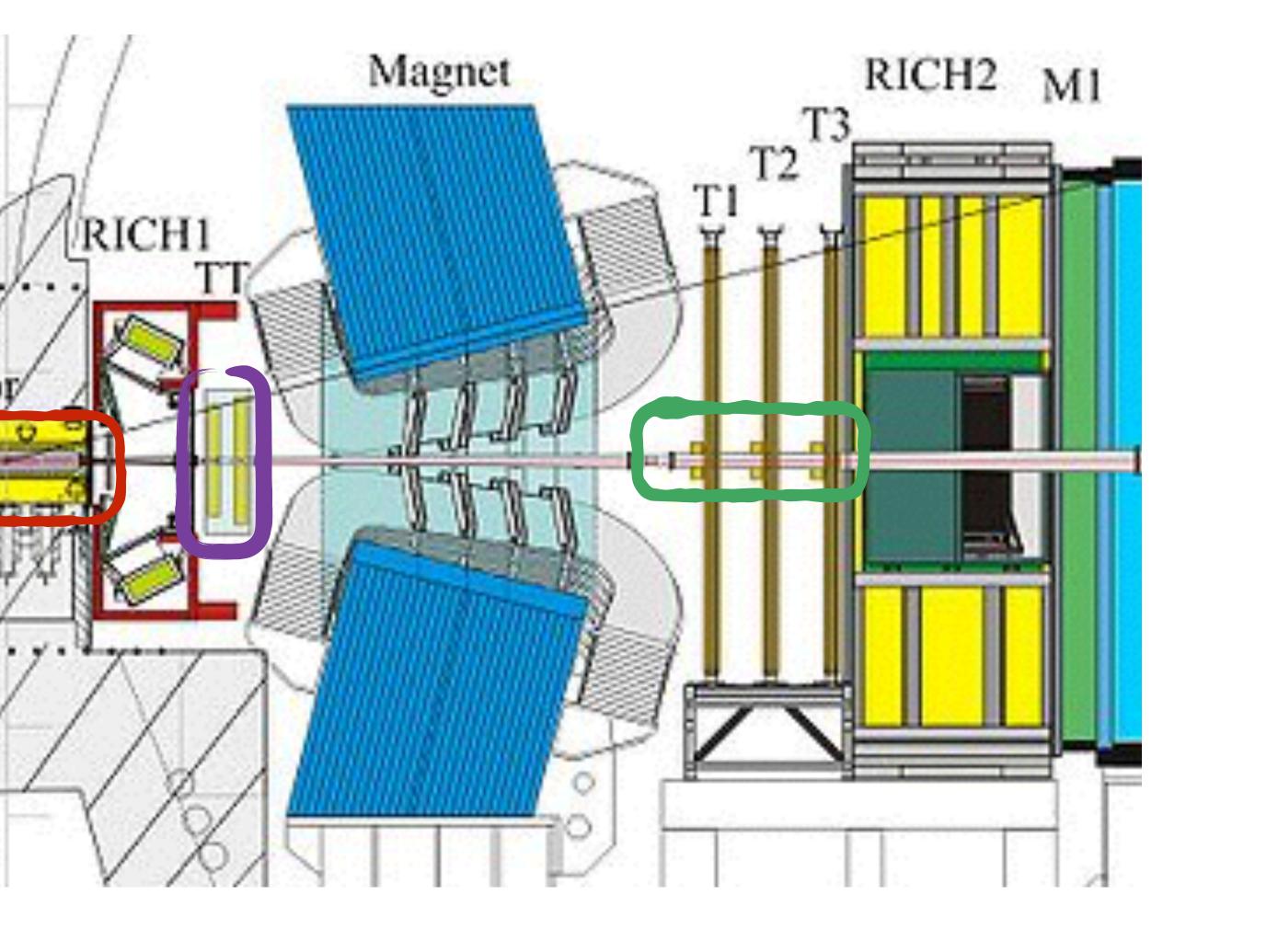
Tracker Turicensis

Inner Tracker (||)





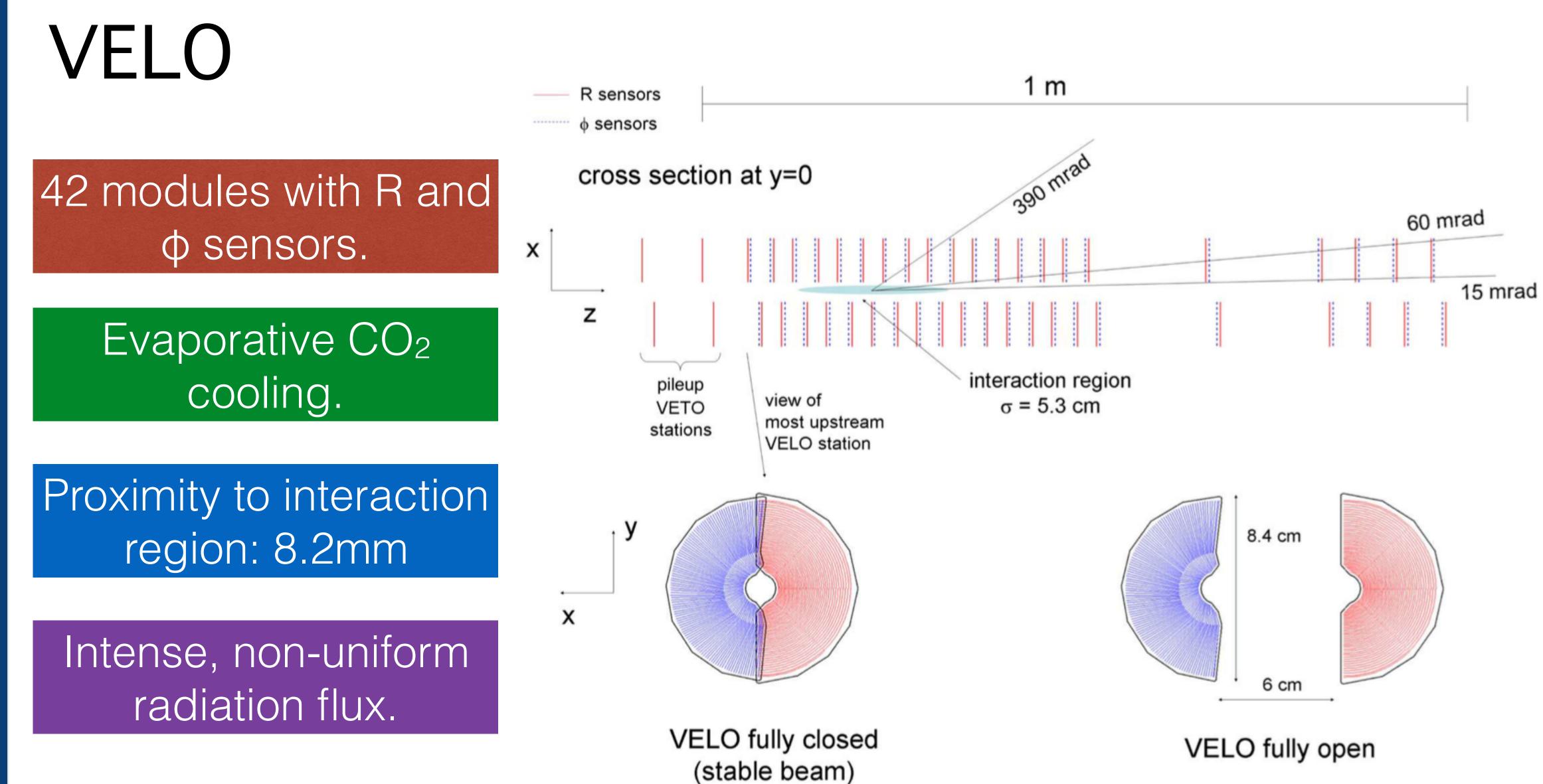
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Int. J. Mod. Phys. A **30**, 1530022 (2015)









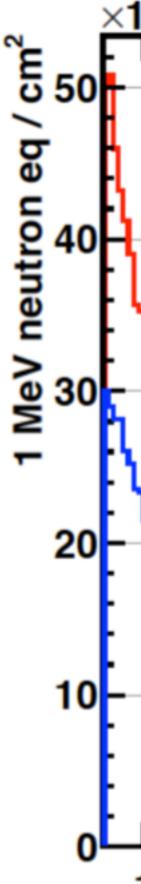


VELO

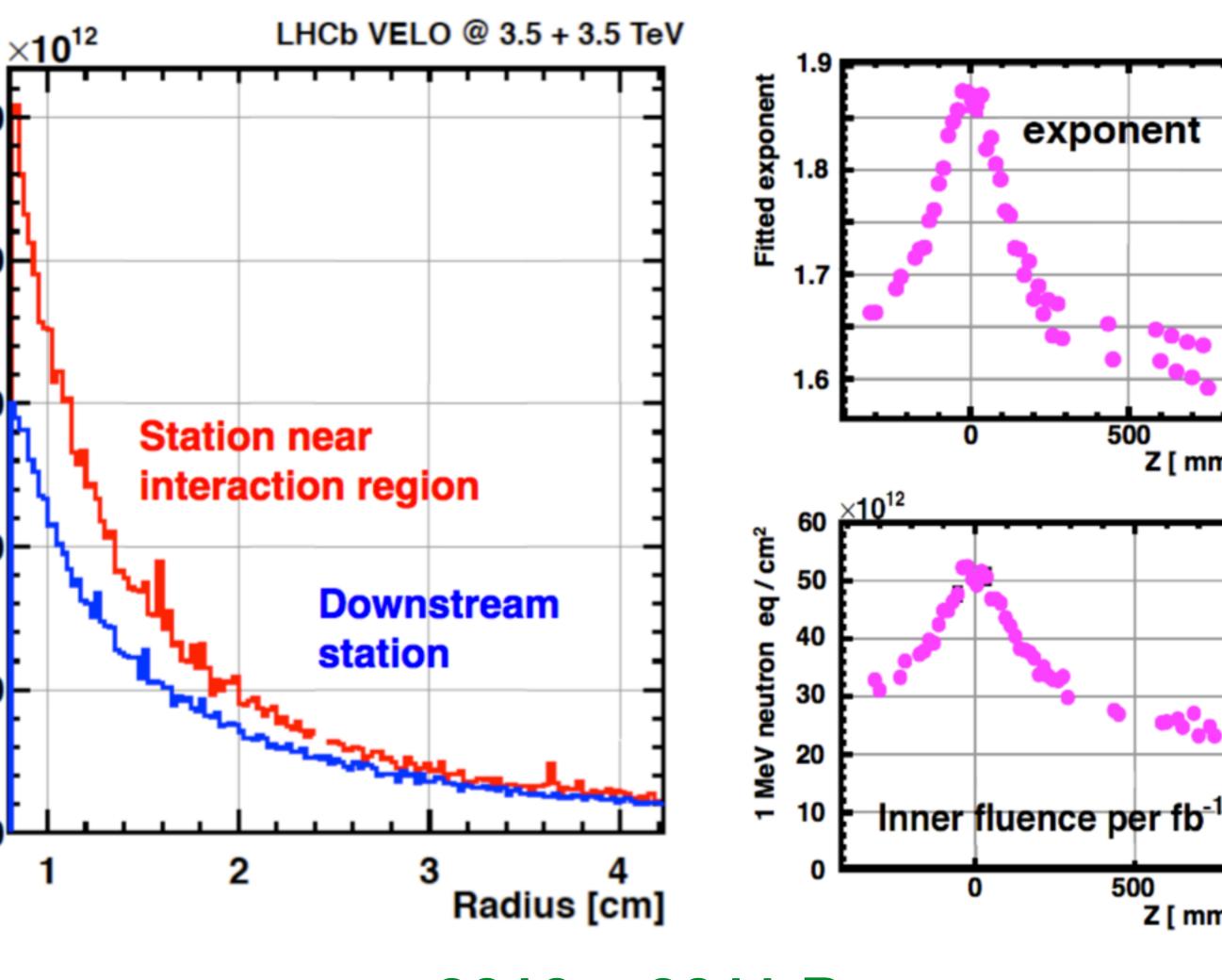
Expected fluence in the most irradiated regions up to 5x10¹³ 1MeV n_{eq}/cm²

Radiation flux follows r^{-1.9} shape.

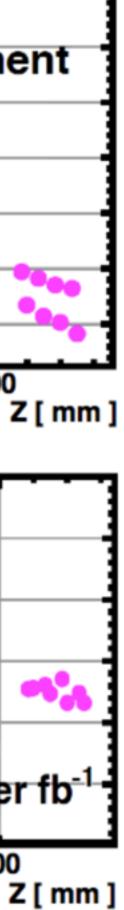
Proximity to interaction region: 8.2mm







2010 + 2011 Data





VELO

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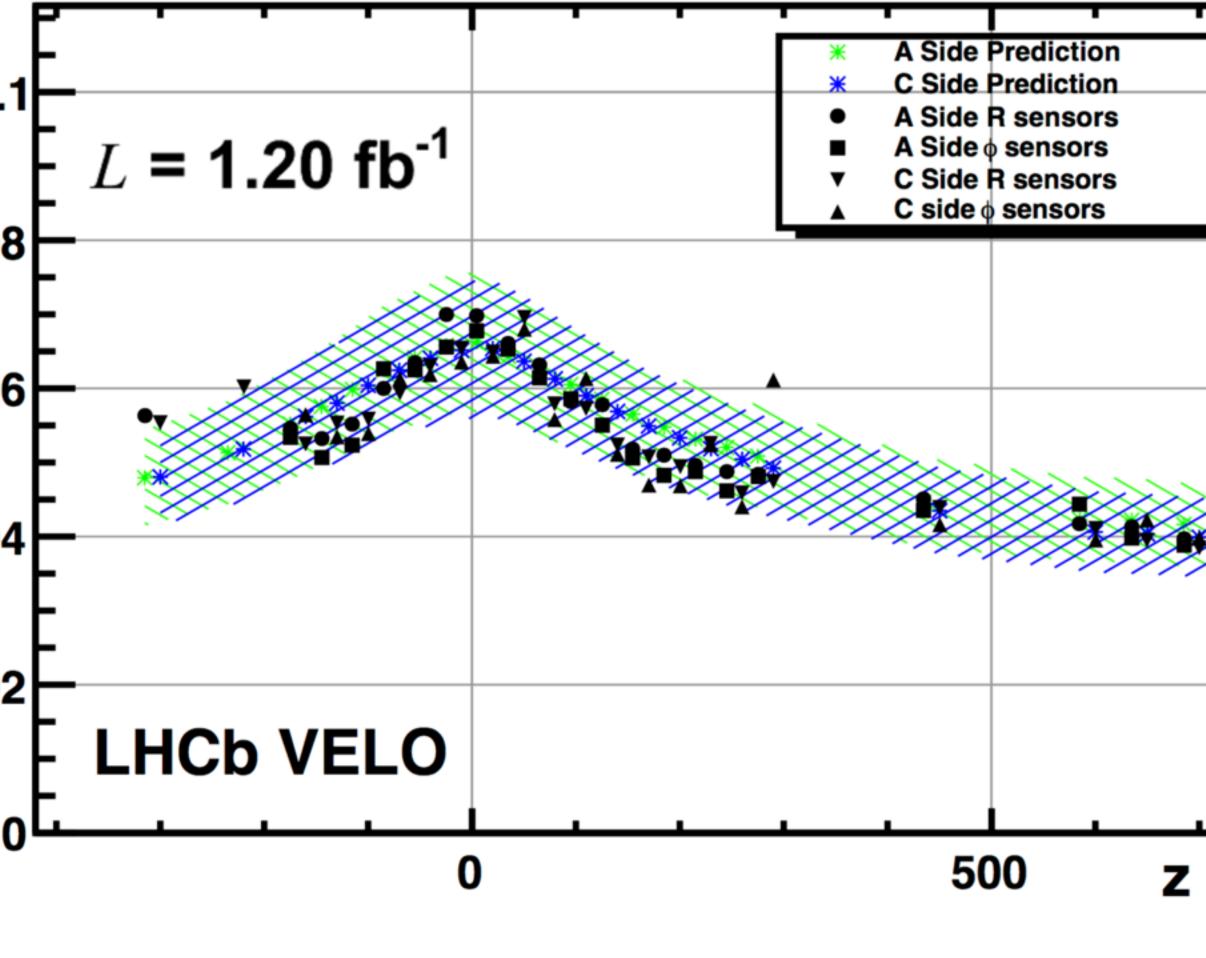
Proximity to interaction region: 8.2mm

Current [mA 0.1 0.08 0.06

0.04

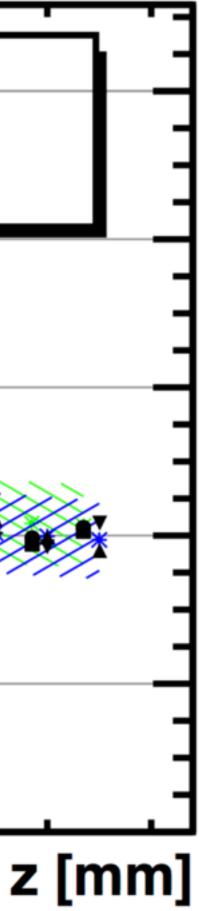
0.02



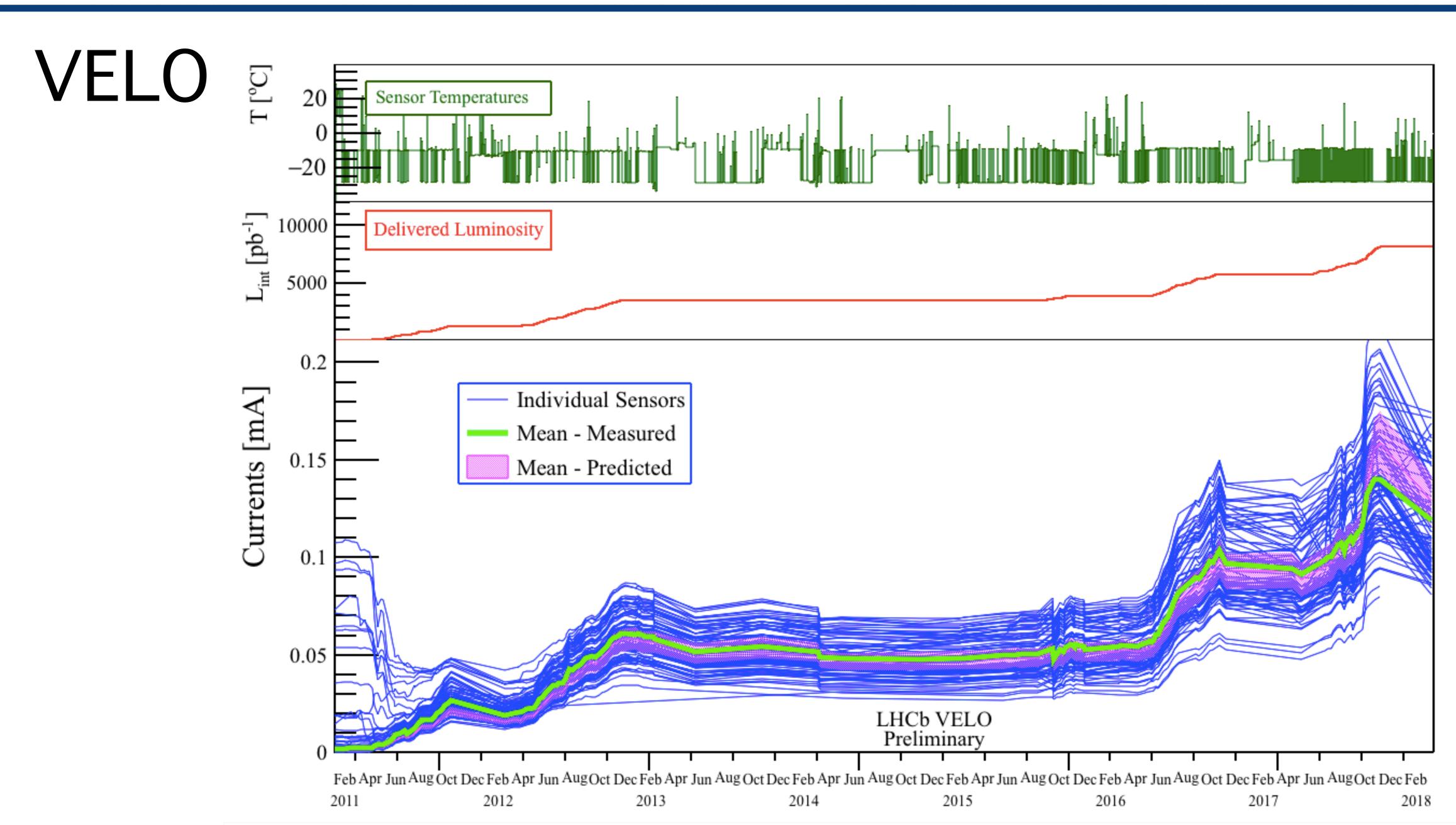


2010 + 2011 Data





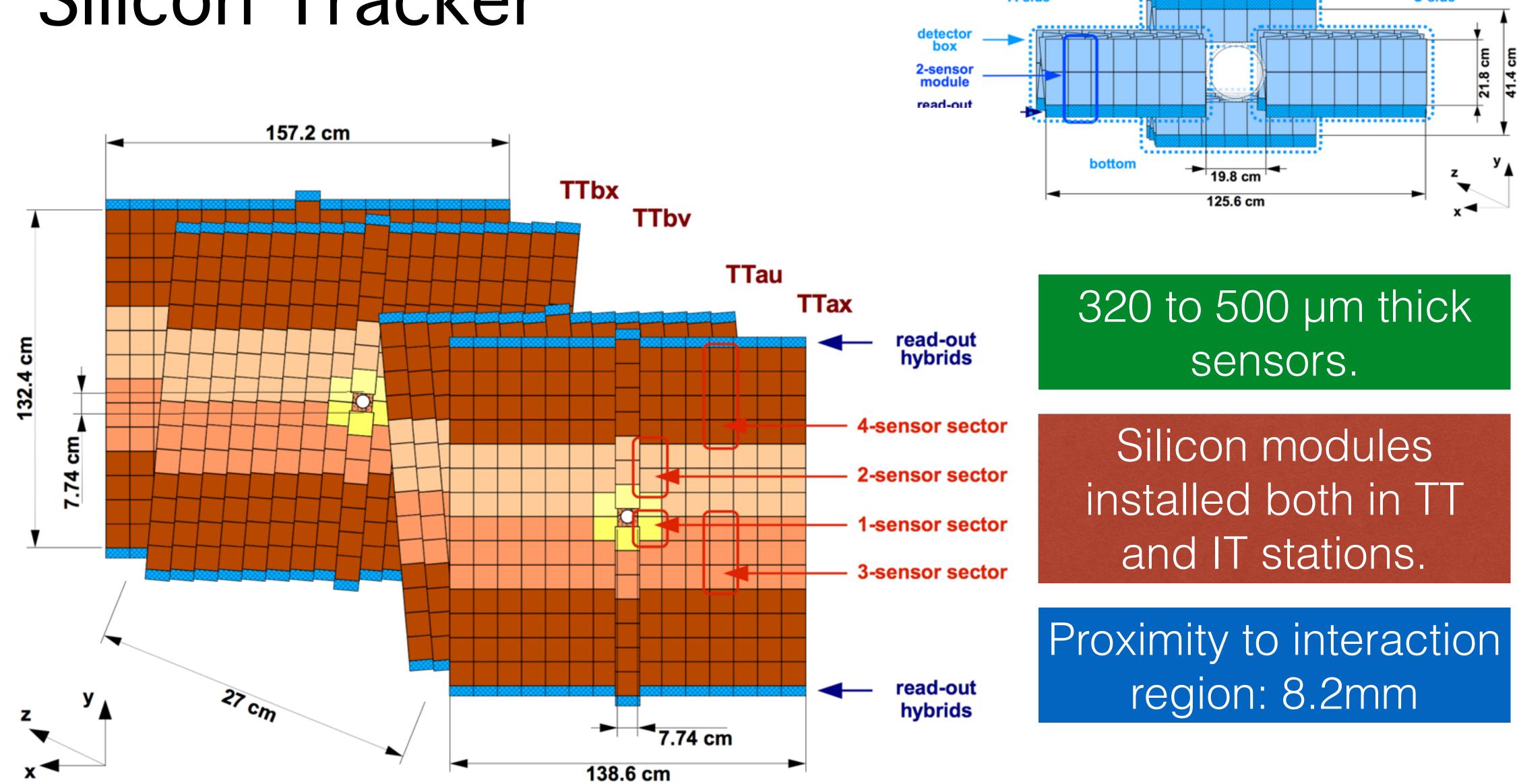




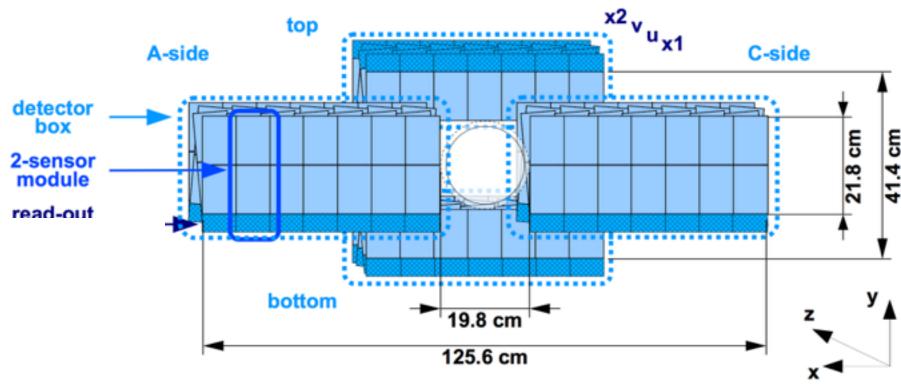




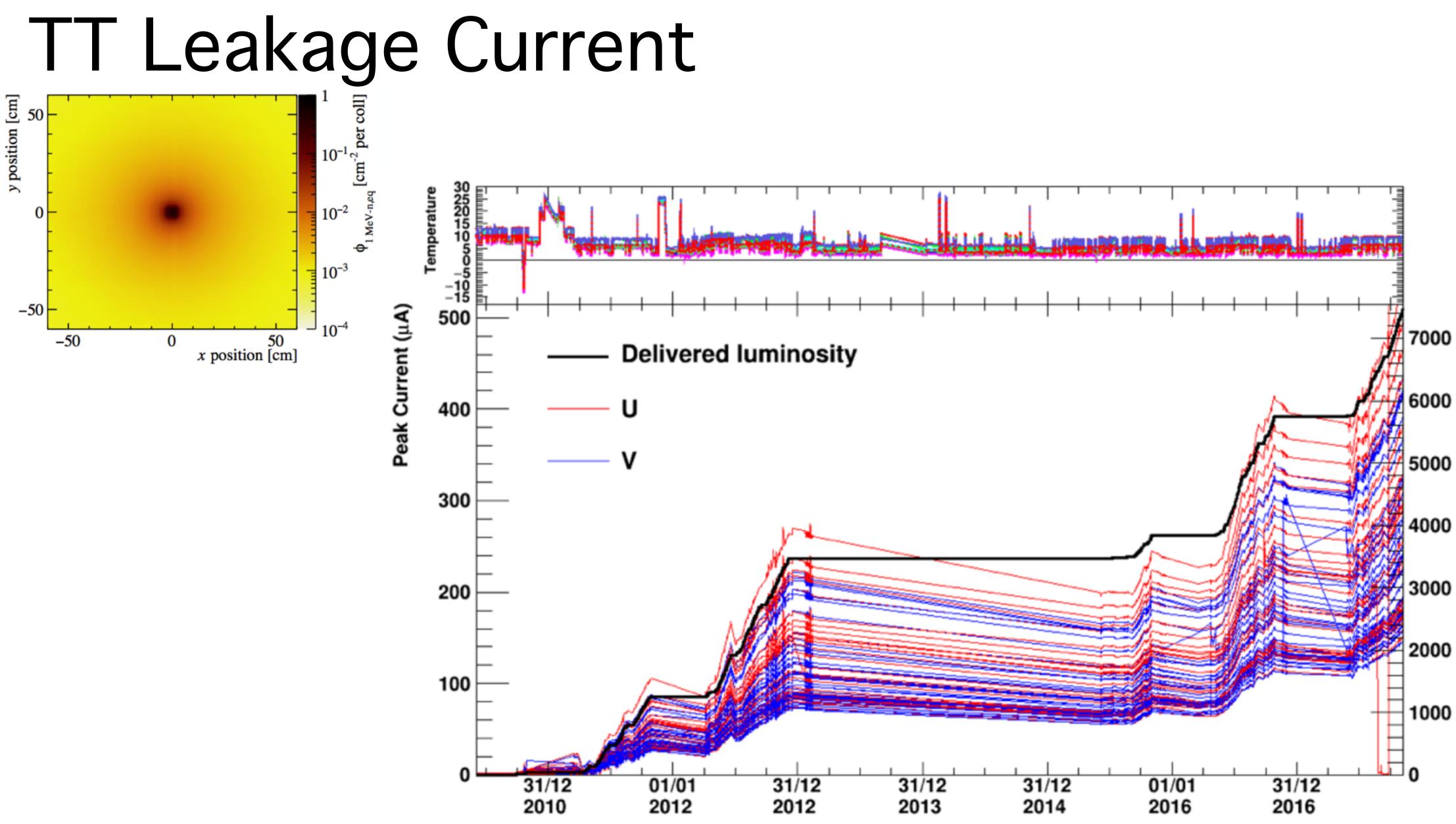
Silicon Tracker















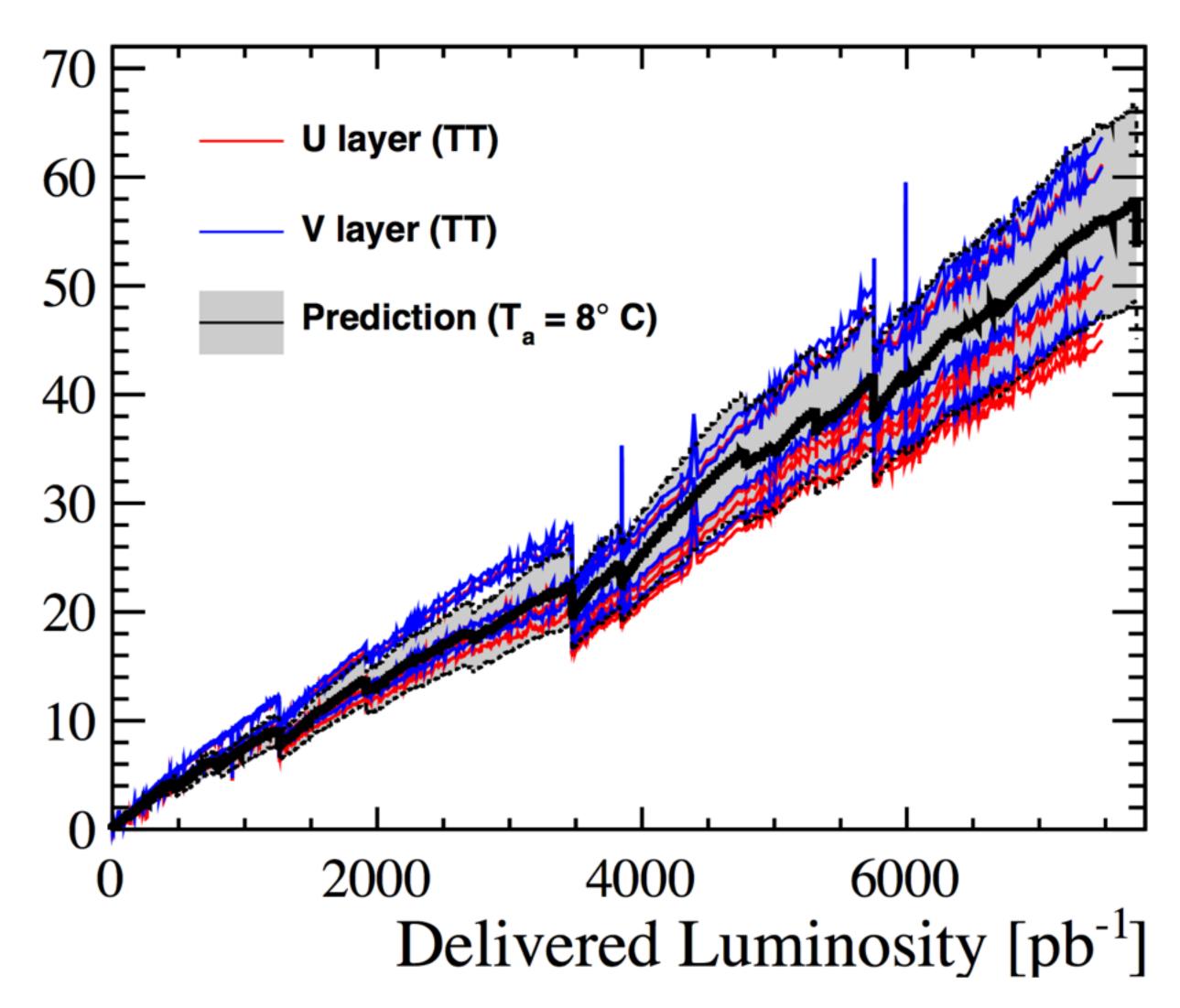


ST Leakage Current

Current is defined as peak current per sensor per fill.

Shown here is the prediction based on the expected does and annealing periods. $[A/m^3]$ leak//









The VELO Upgrade

Full 40 MHz readout.

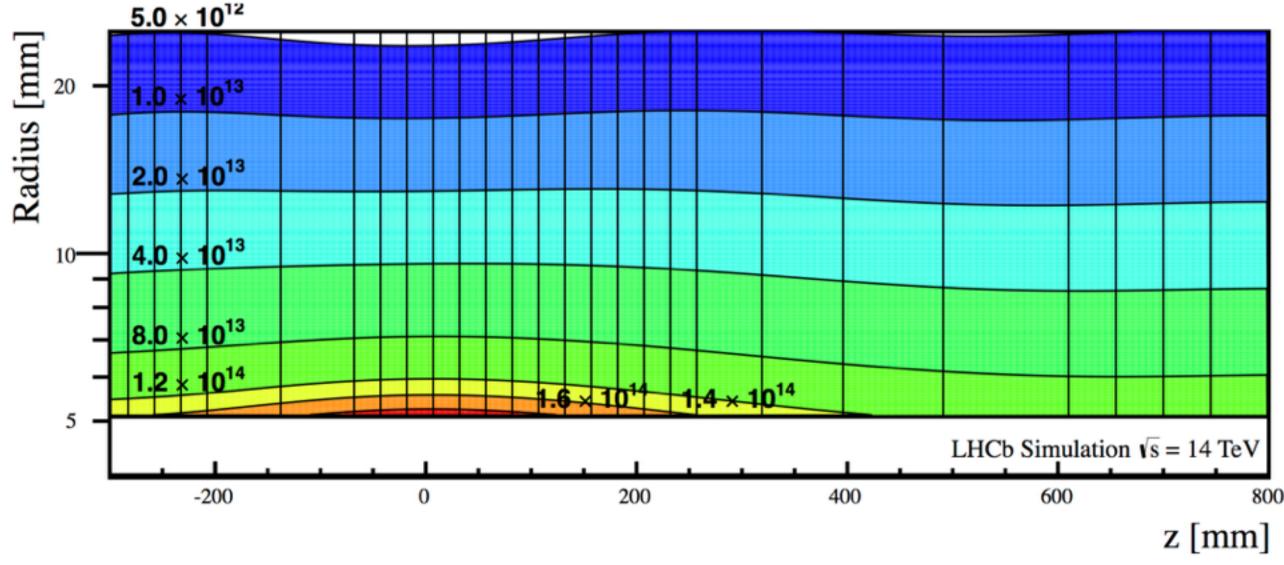
Closest detector to interaction point (5.1mm). Non-Uniform radiation flux.

Data Bandwidth of 20 Gbit/s for central ASICS.

Microchannel CO2 cooling, sensor temperature <-20°C



29 mm movement C-side









VELO Upgrade

Expected fluence in the most irradiated regions up to 1.5x10¹⁴ 1MeV n_{eq}/ cm² per fb⁻¹

Radiation flux follows r^{-2.3} shape.

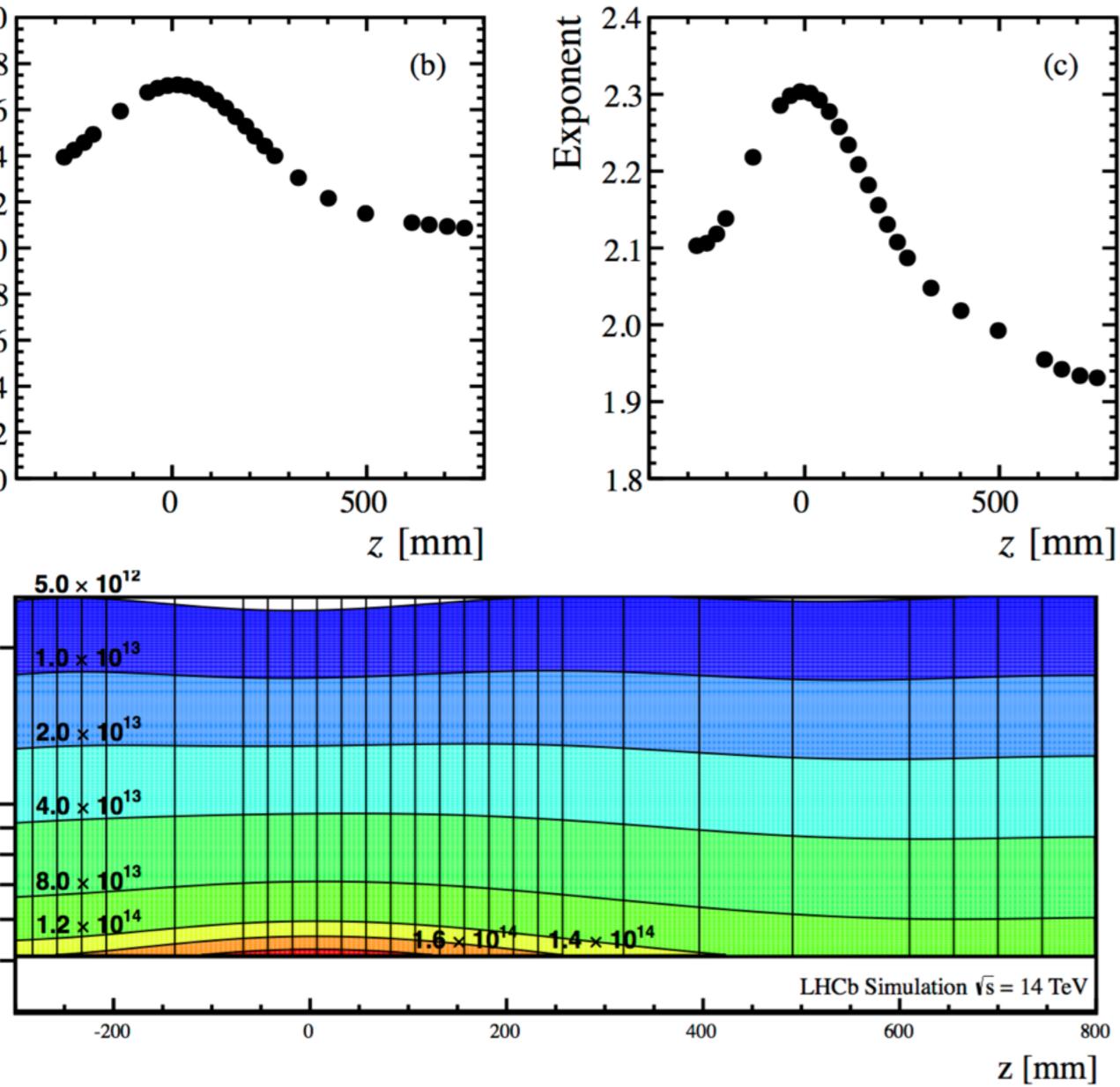
Proximity to interaction region: 5.1mm

Total Integrated Luminosity: 50fb⁻¹ !

 cm^{-2}] 10¹⁴ 1 MeV n_{eq} (0.8 0.6 E 0.0 × 0.4 0.2 0.0 Radius [mm]

5









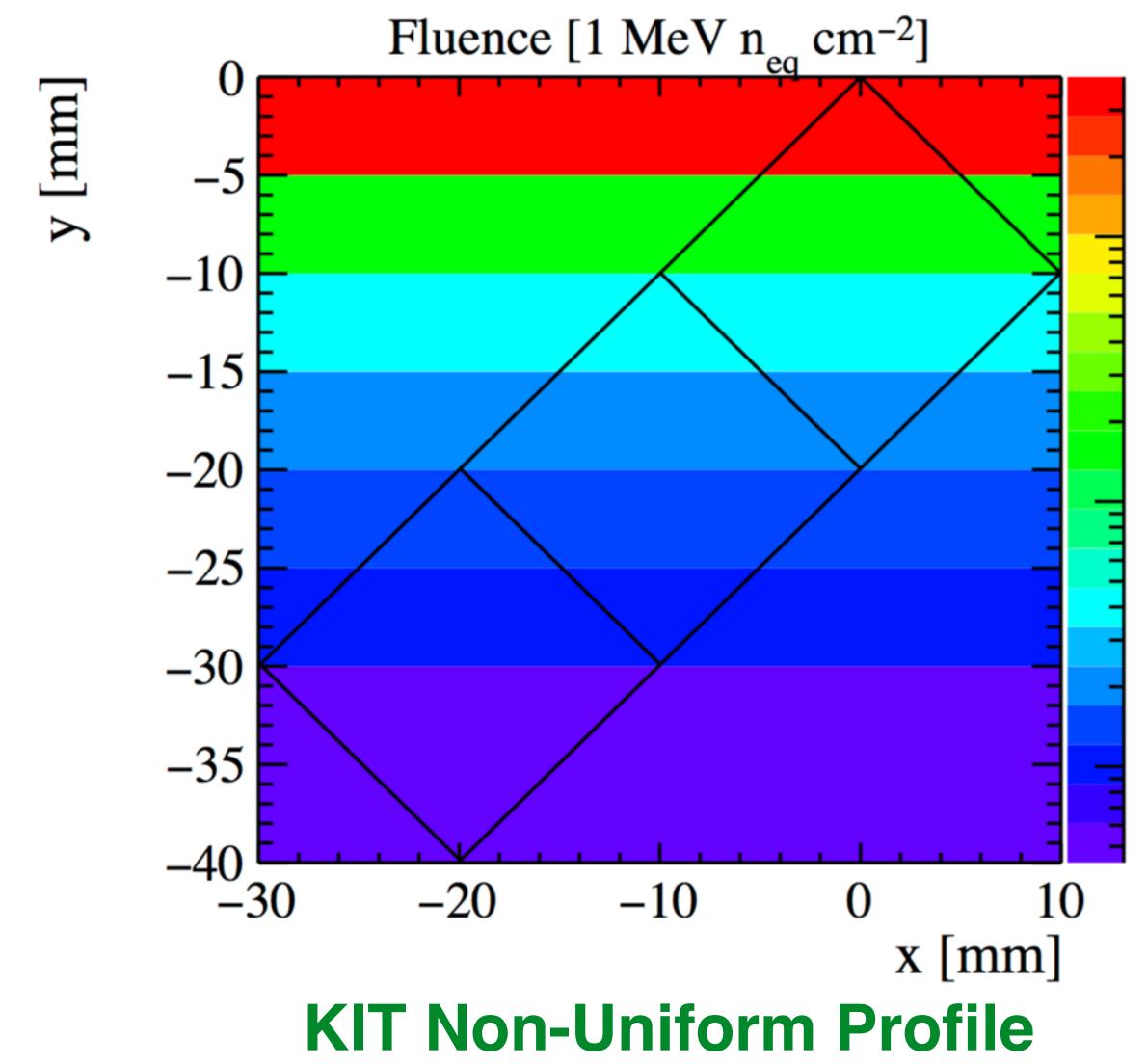
Irradiation

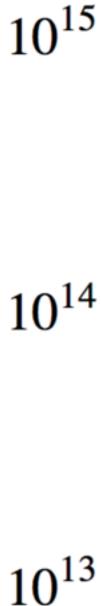
Different Irradiation campaigns were performed.

Goal was to confirm the radiation hardness up to 8x10¹⁵ 1MeV n_{eq}/ cm²

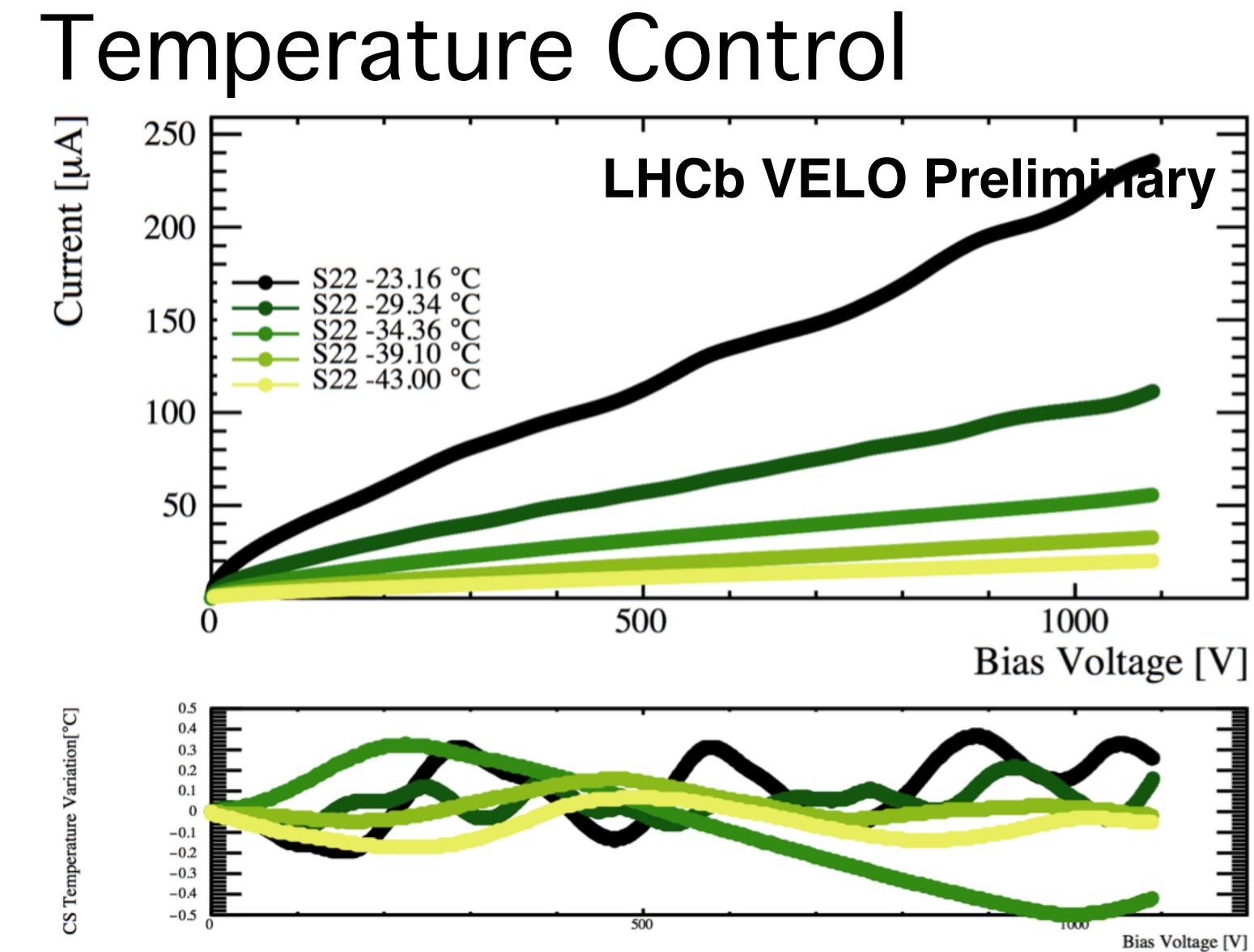
Protons and neutrons uniformly and nonuniformly.













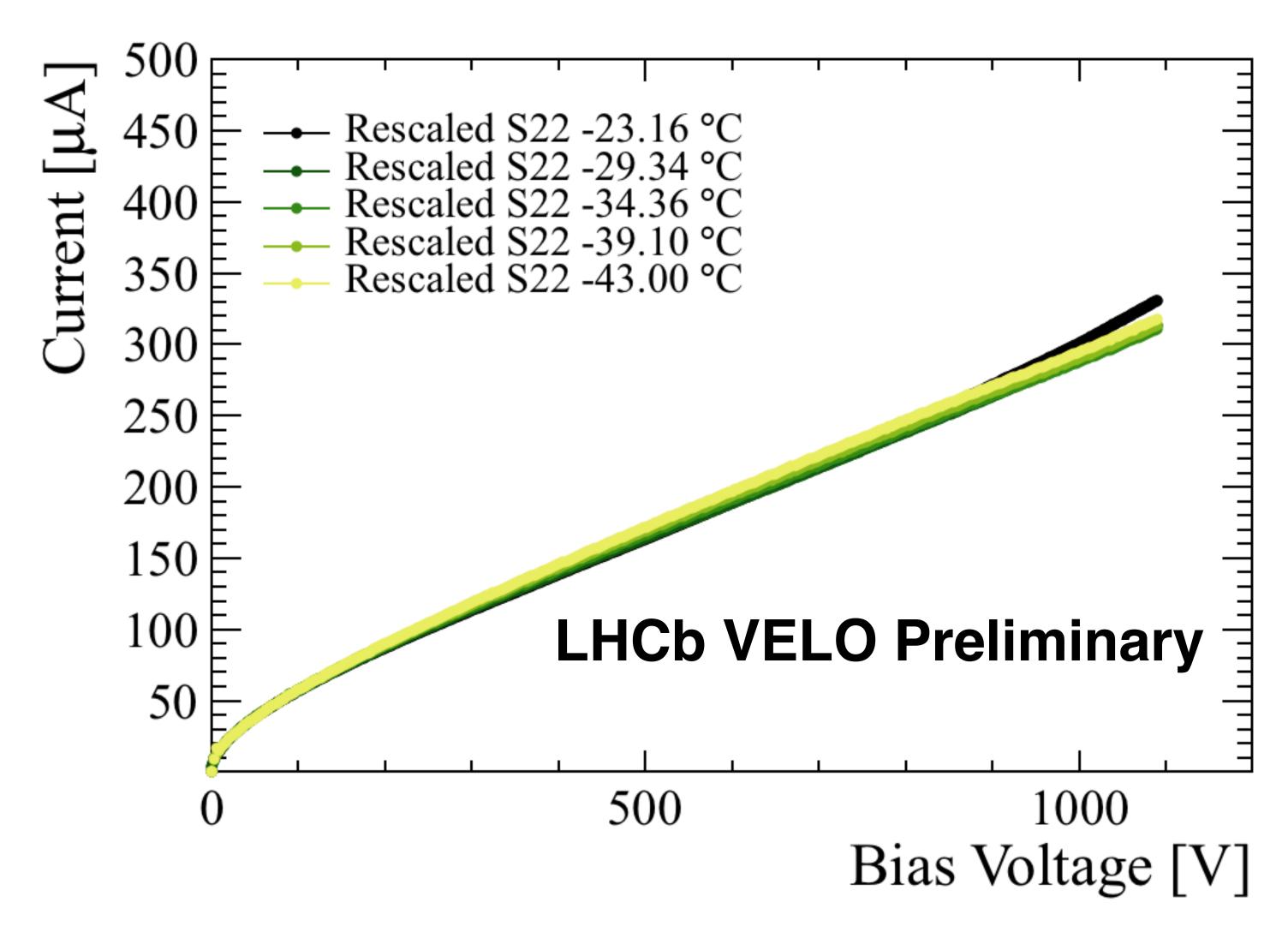
Looking at correlation between the small temperature oscillations in Temperature explains the weird kinks in the IV curves.













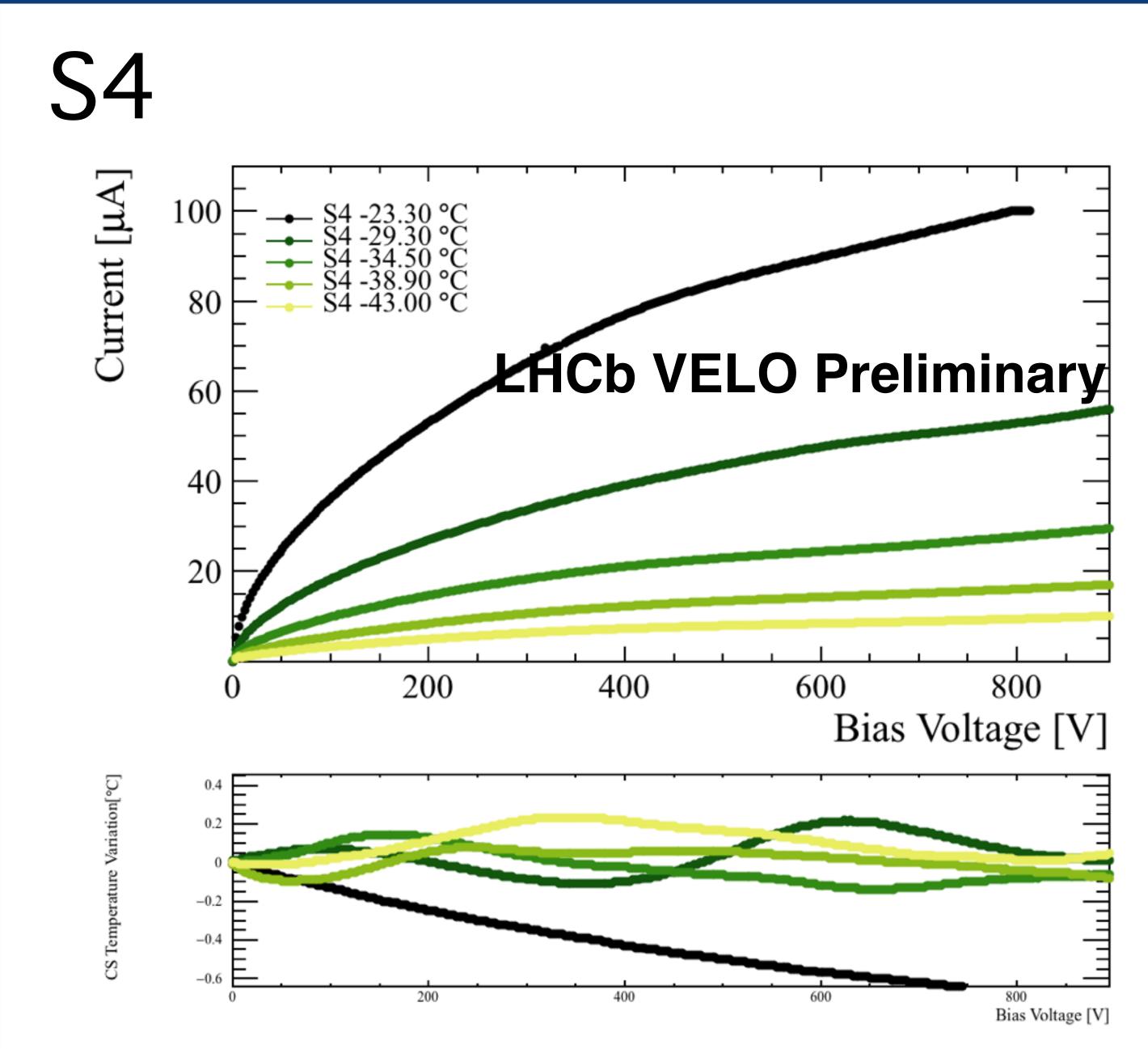
S22 Full Fluence Uniformly irradiated with neutrons at JSI.

Rescaling all IVs to -20°C using the temperature readout removes the kinks and the result seems consistent.











S4 Half Fluence Uniformly irradiated with protons at KIT.

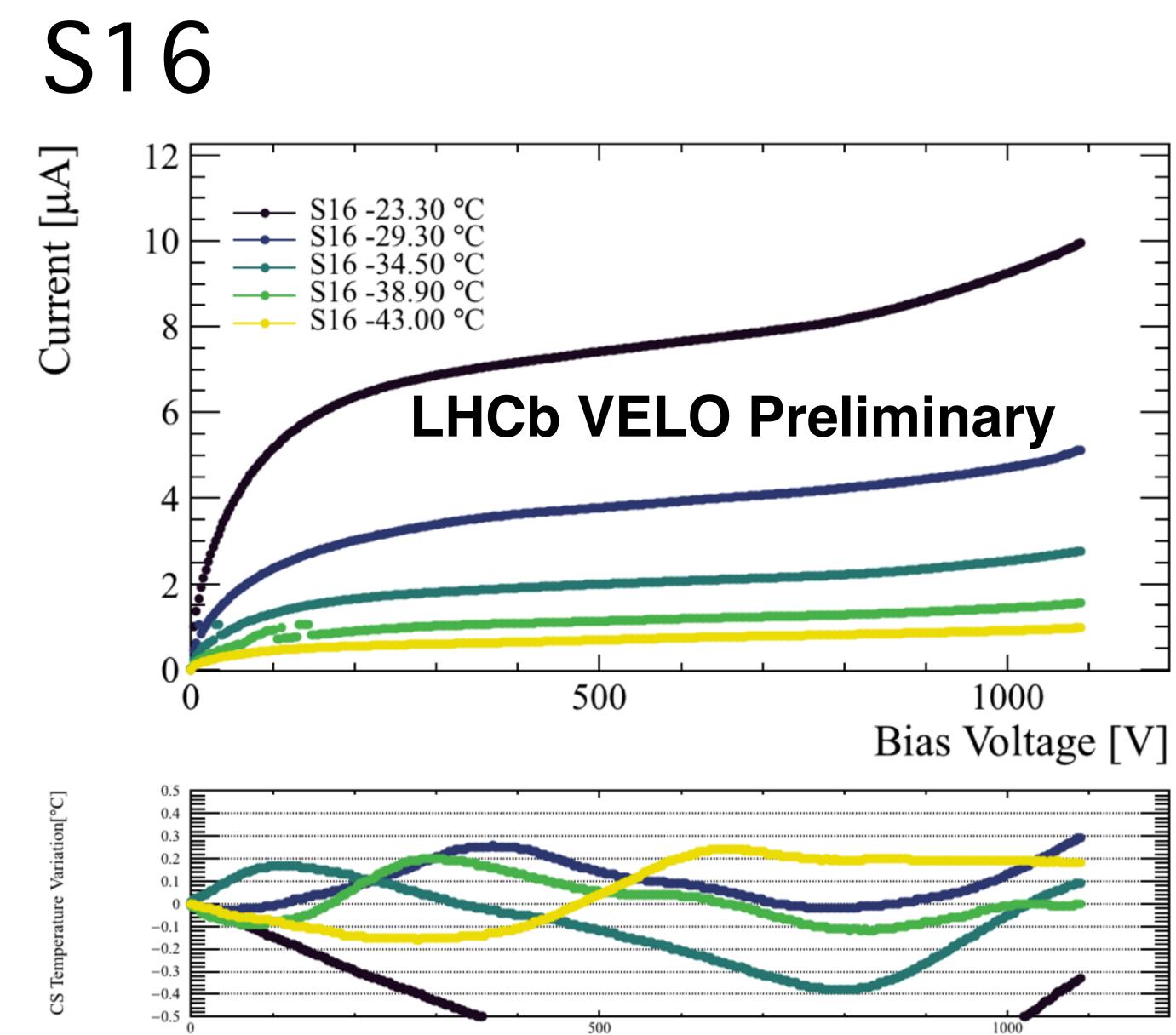
No exponential current behaviour. It doesn't happen for uniformly irradiated.











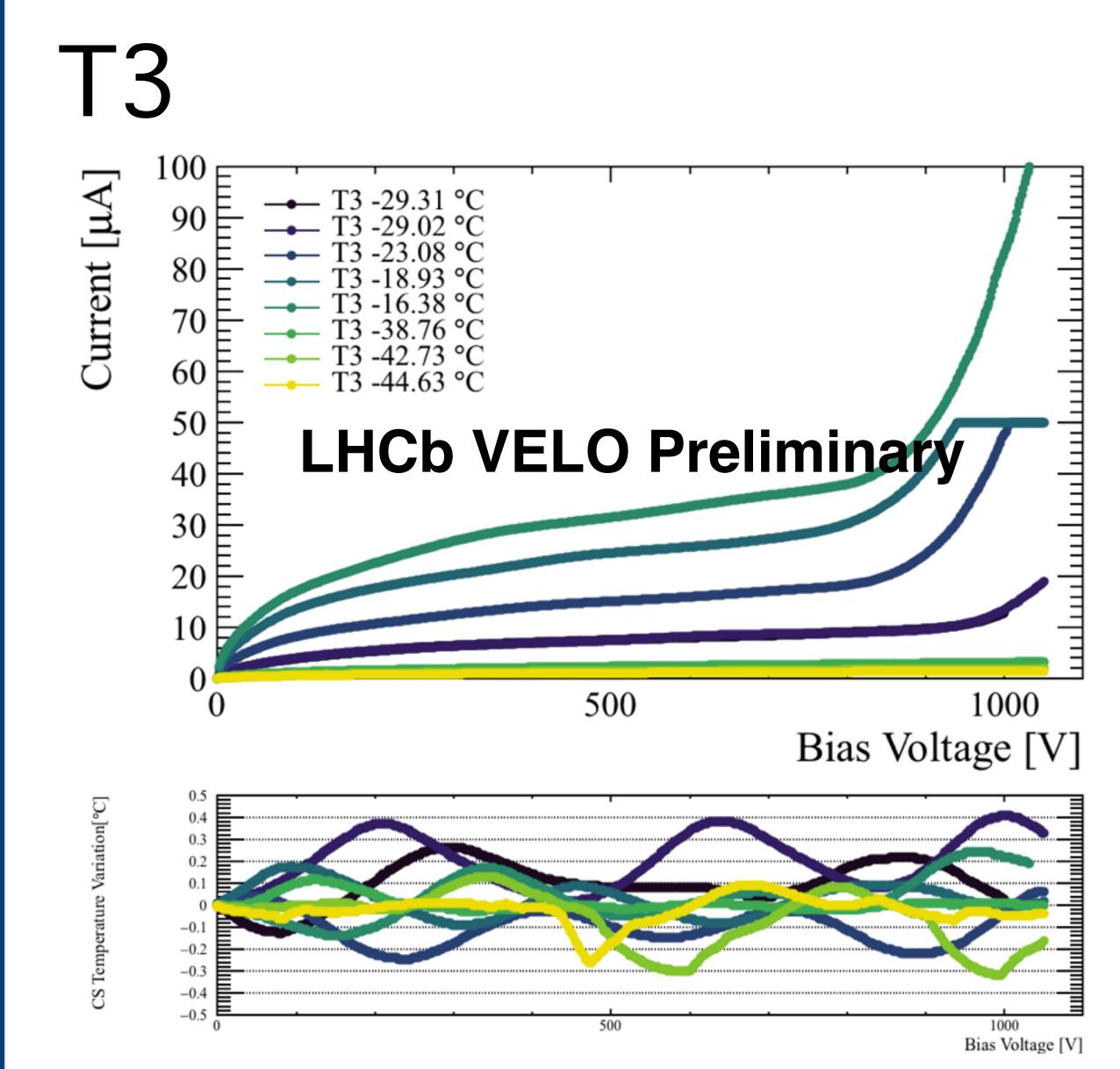


Bias Voltage [V]

S16 Half Fluence Non Uniformly irradiated with protons at KIT.









T3 Full Fluence Non Uniformly irradiated with protons at KIT.





Temperature Dependent Breakdown

Early breakdown was observed at low voltages.

The temperature scan was done in order to understand the effect.

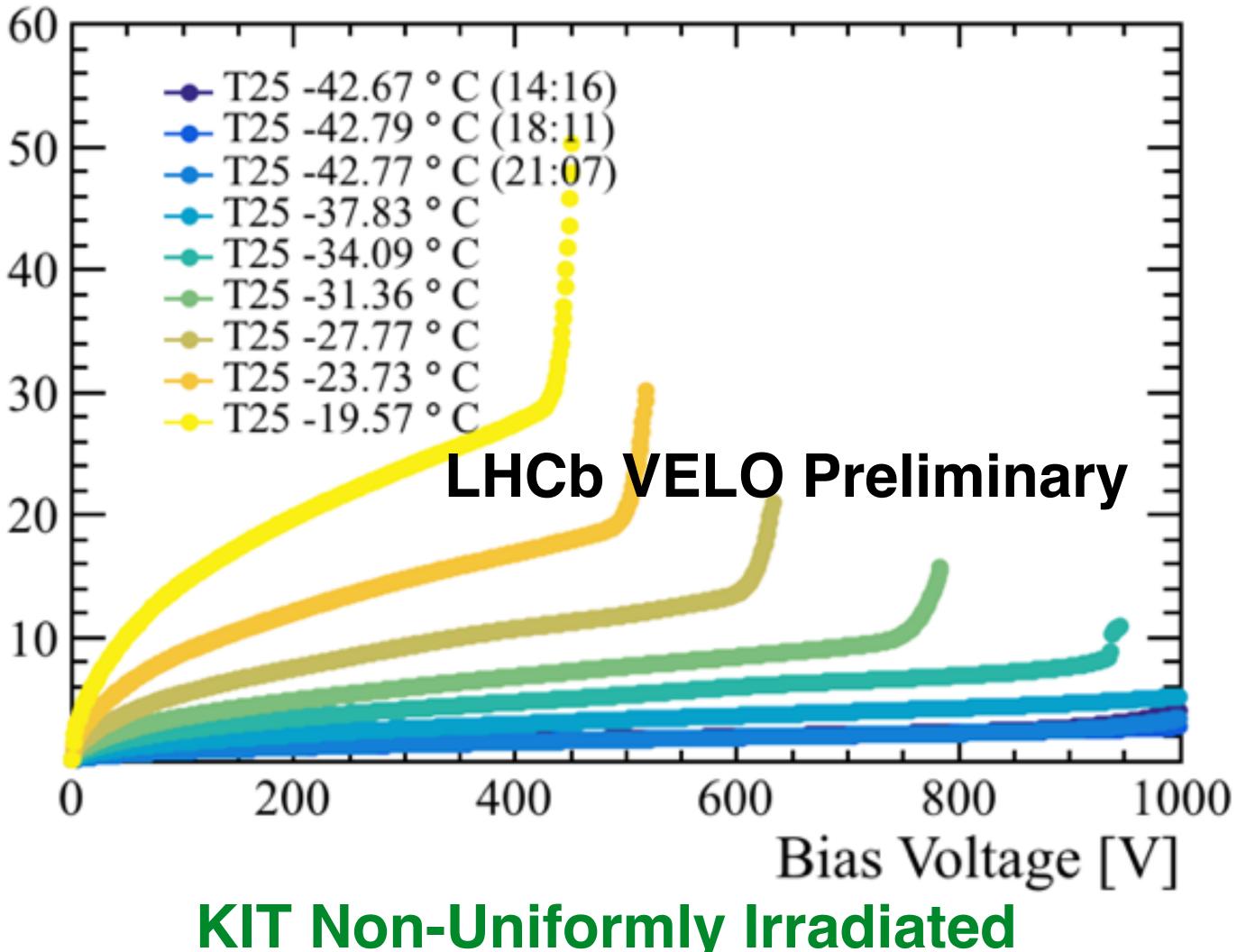
60 Current [µA]

30

20

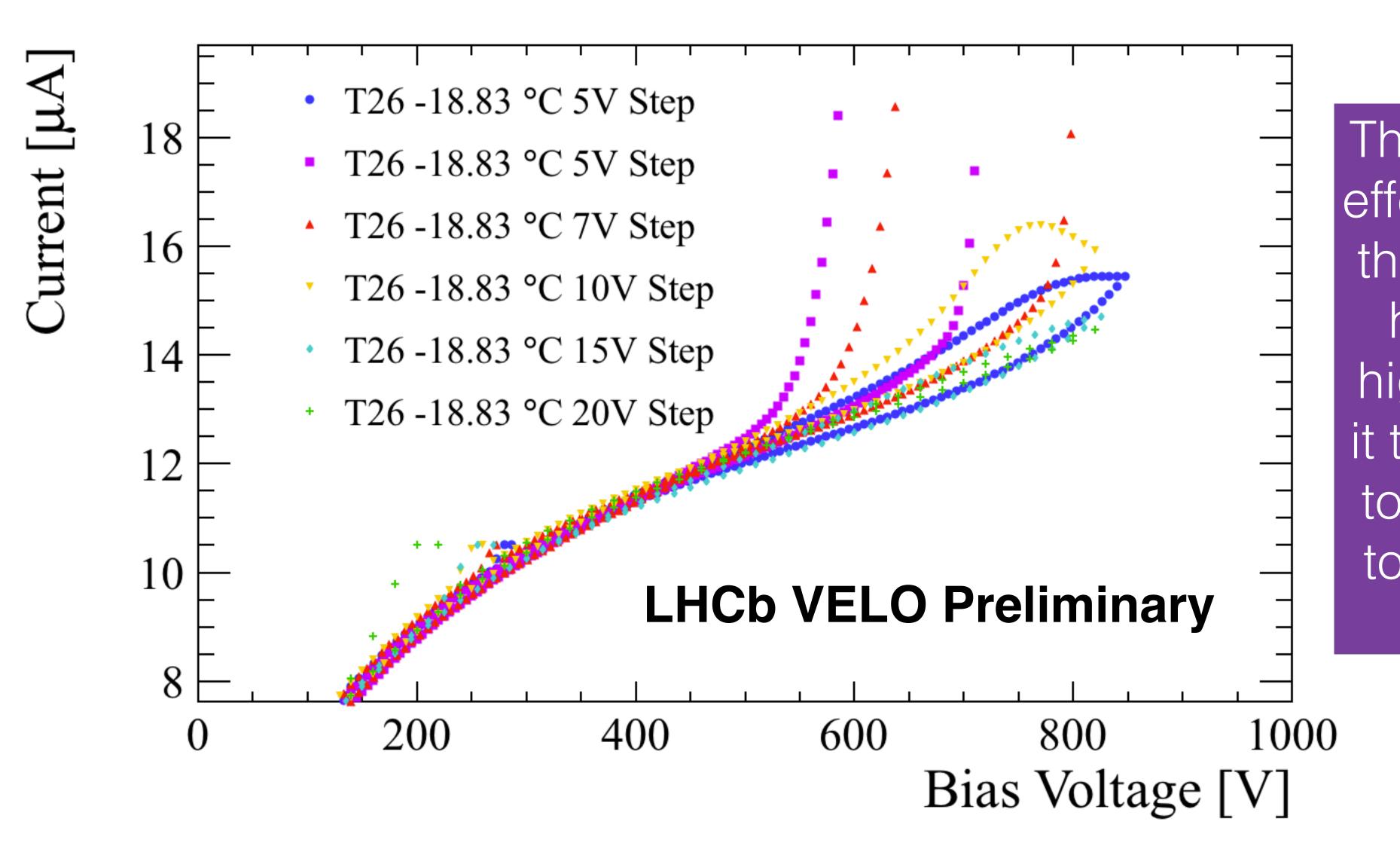
10



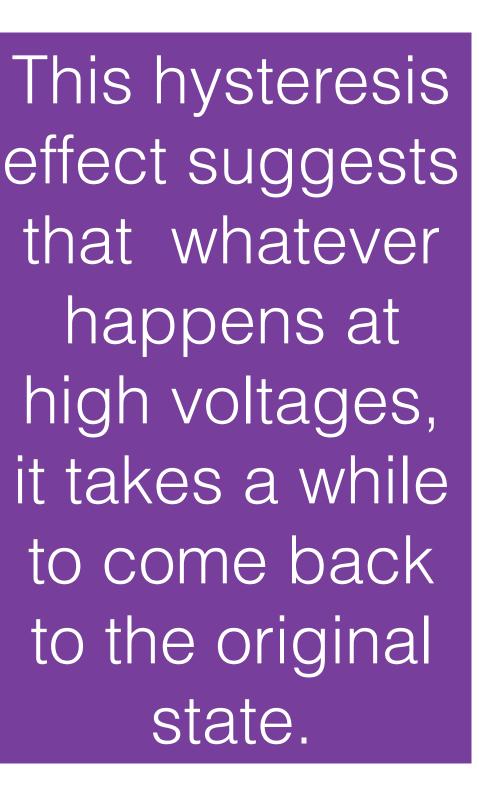




Maybe the approach to BD matters?

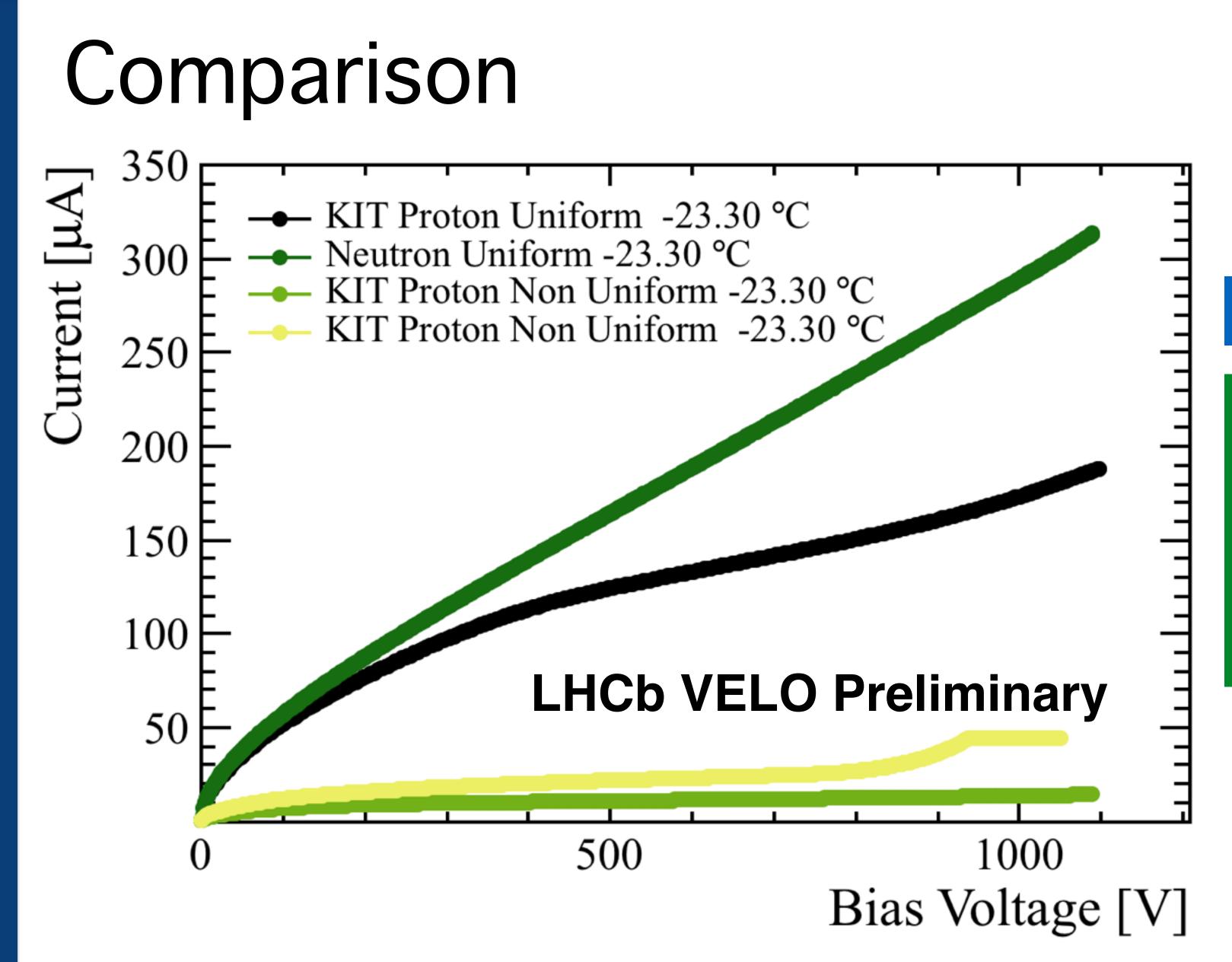






state.







All Scaled to -20°C.

Different Radiation dose to each one depending on uniformity / max fluence.

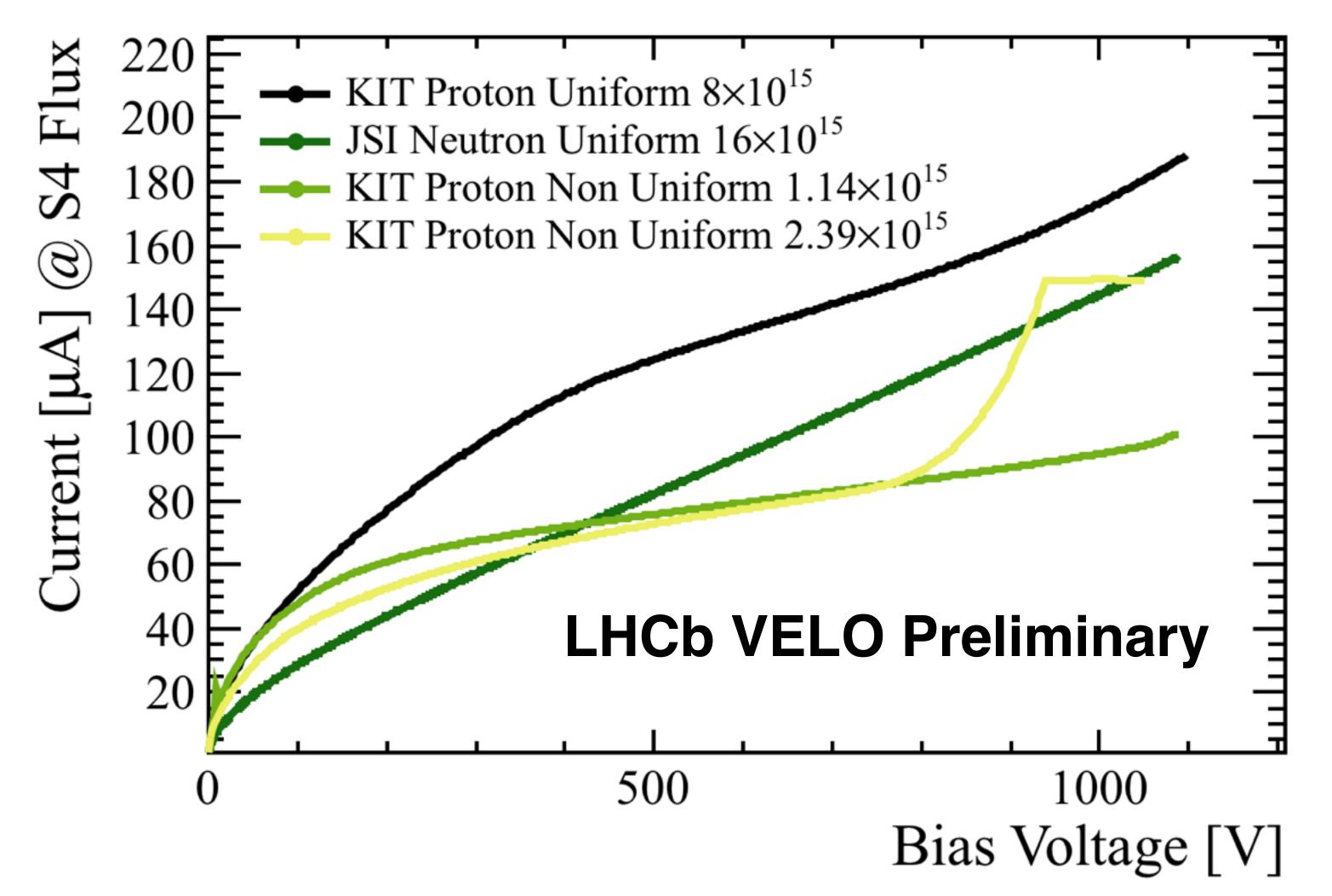








Comparison





All Scaled to -20°C.

Absolute values are very similar, although some features seem slightly different.

Scaling between different irradiations seem to hold well.











This project has received funding from the European Union's Horizon 2020 research and innovation programme under grant agreement No 654168

Conclusion

VELO will operate during 2018, entering beyond design integrated luminosity region in great shape.

TT and IT leakage current evolution are also evolving as expected.

Interesting effects observed in some of the irradiated sensors for the VELO Upgrade under investigation. New proton non uniform Irradiation being performed in the MC40 facility at Birmingham.



VELO expected leakage current evolution follow expected behaviour from radiation damage.



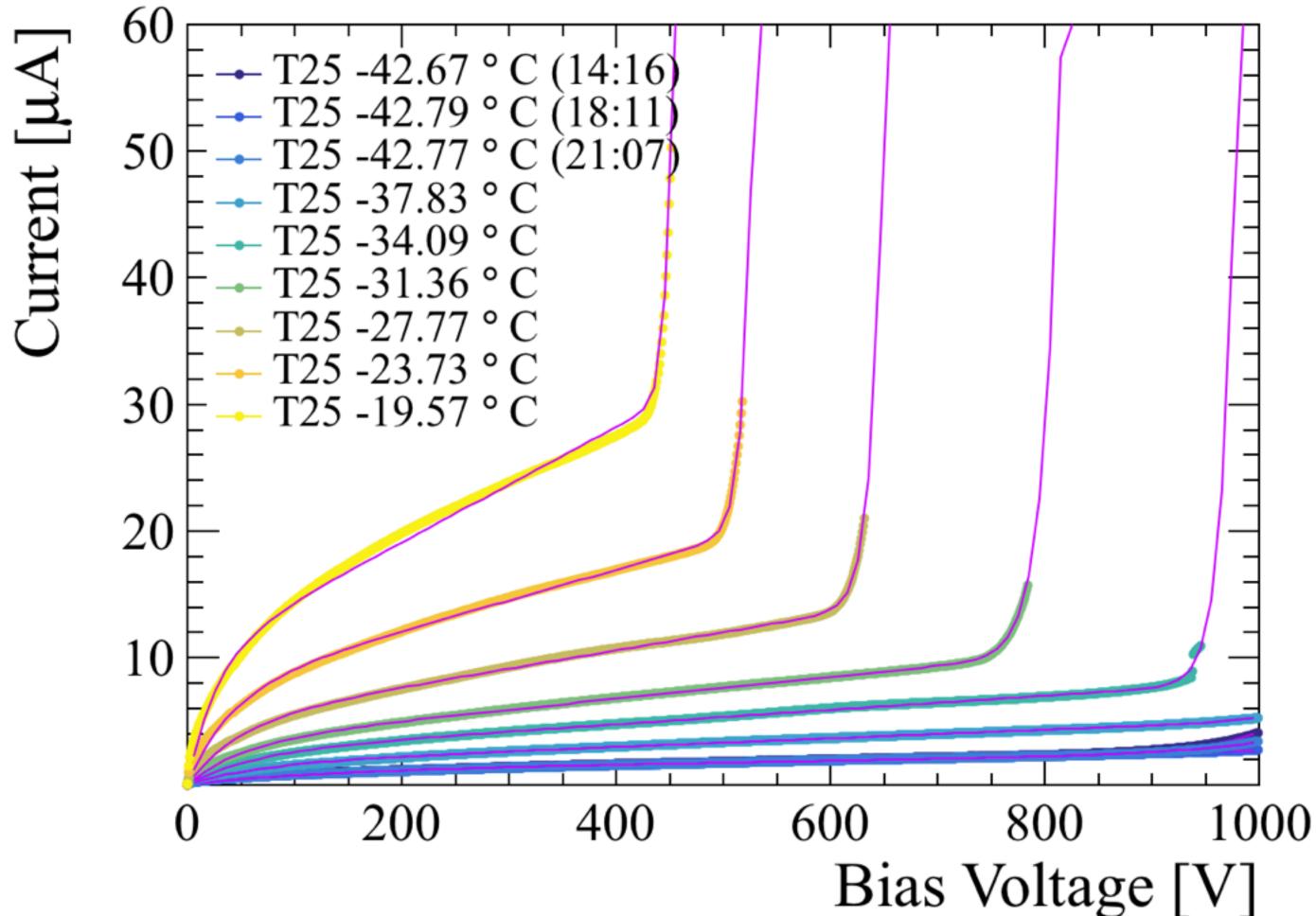


Backup





Modelling breakdown



Current [µA]

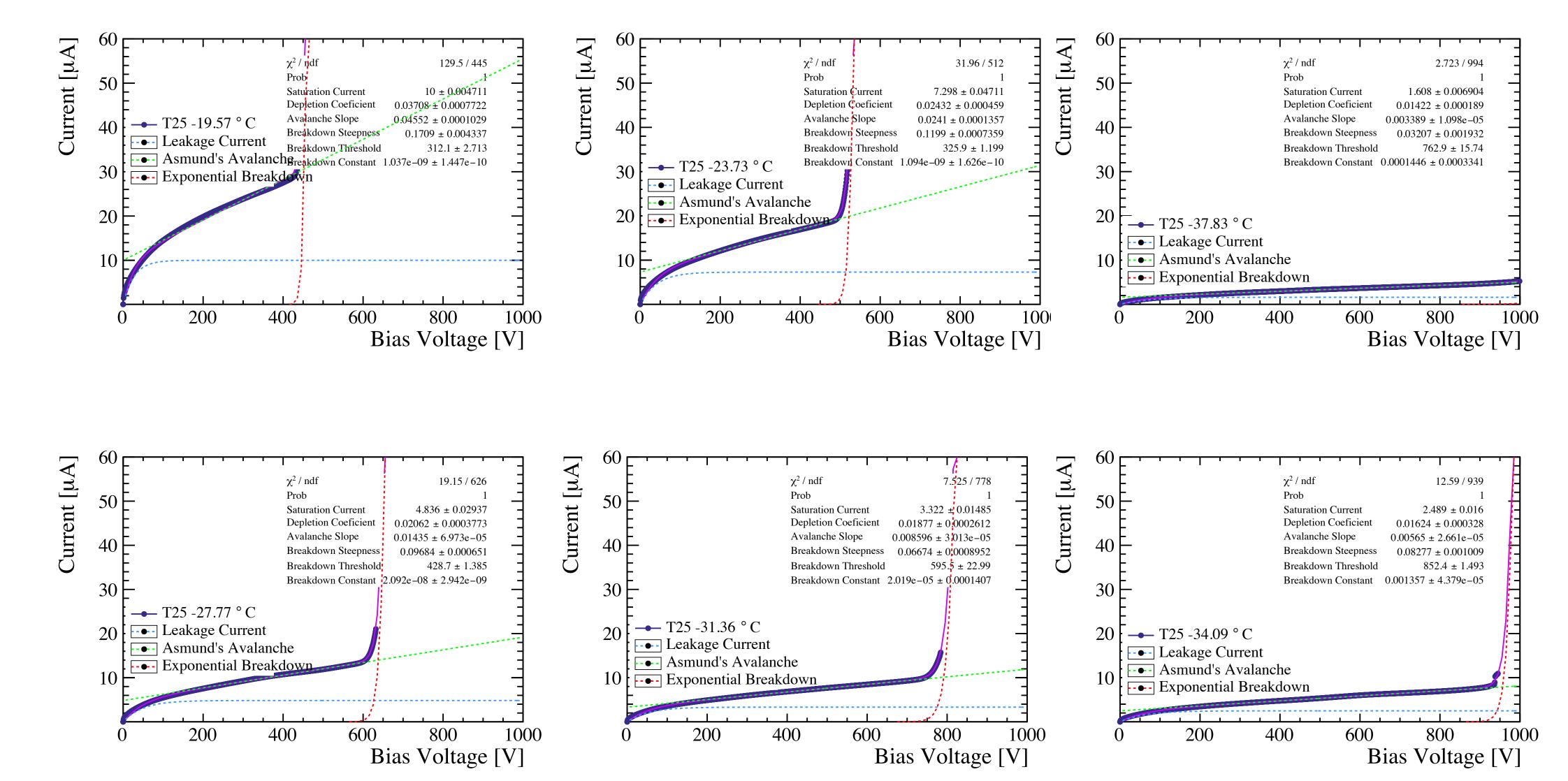


IV curve comprised of three terms

Define breakdown as the point in which the exponential term is 10% of the saturation current.



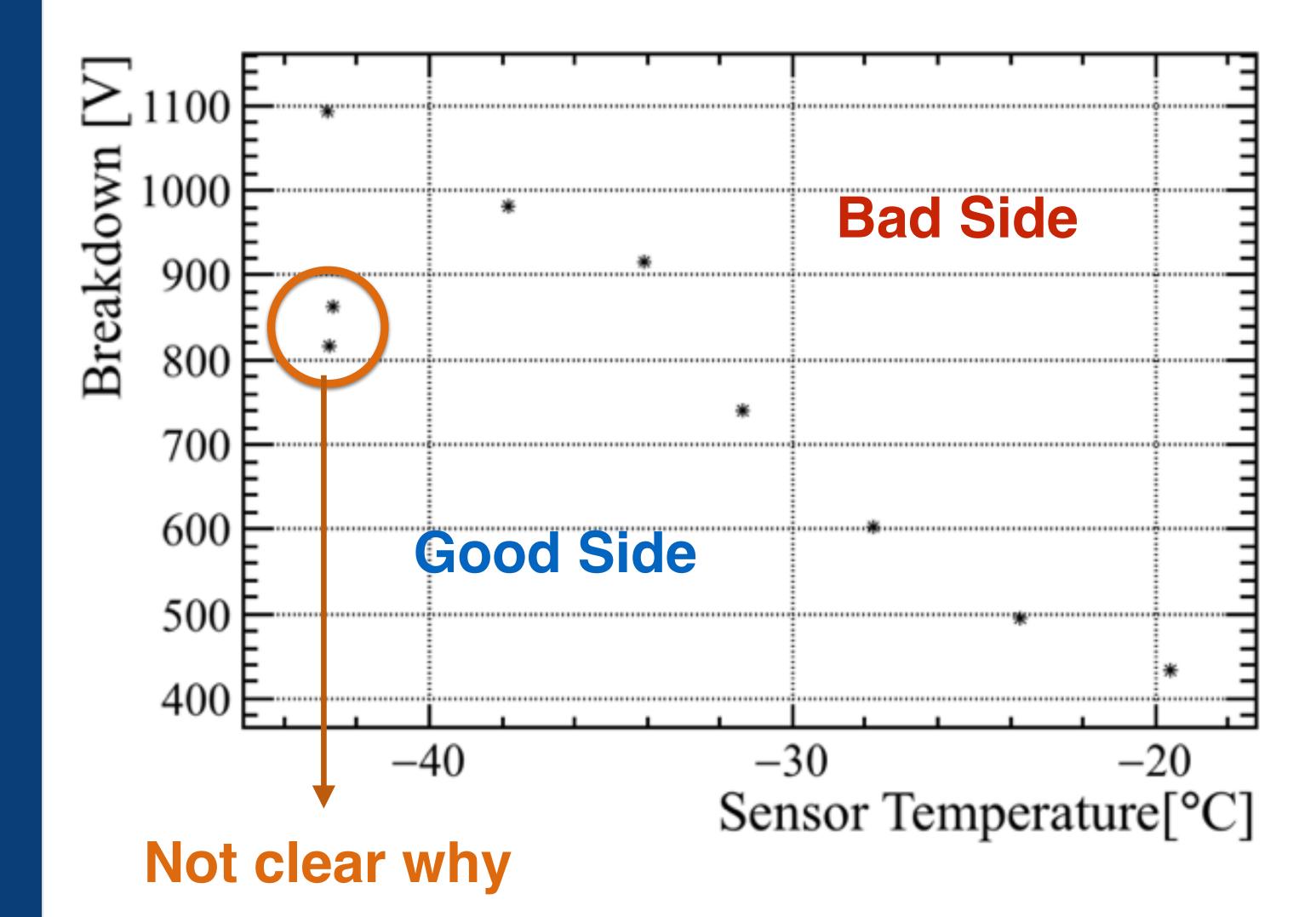
Modelling breakdown







Breakdown x Temperature





BD Voltage definitely depends on temperature.

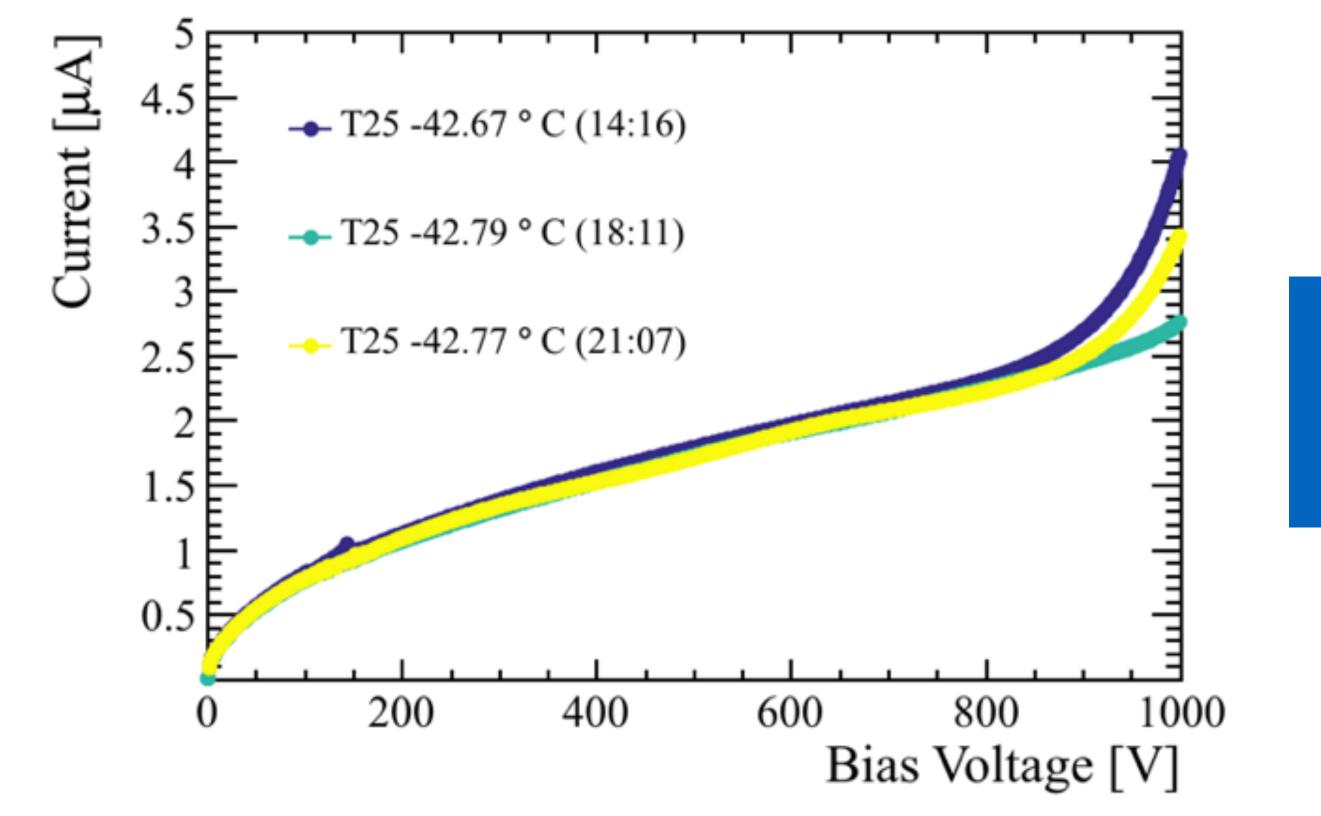
However it seems not very deterministic







Temperature Dependent Breakdown



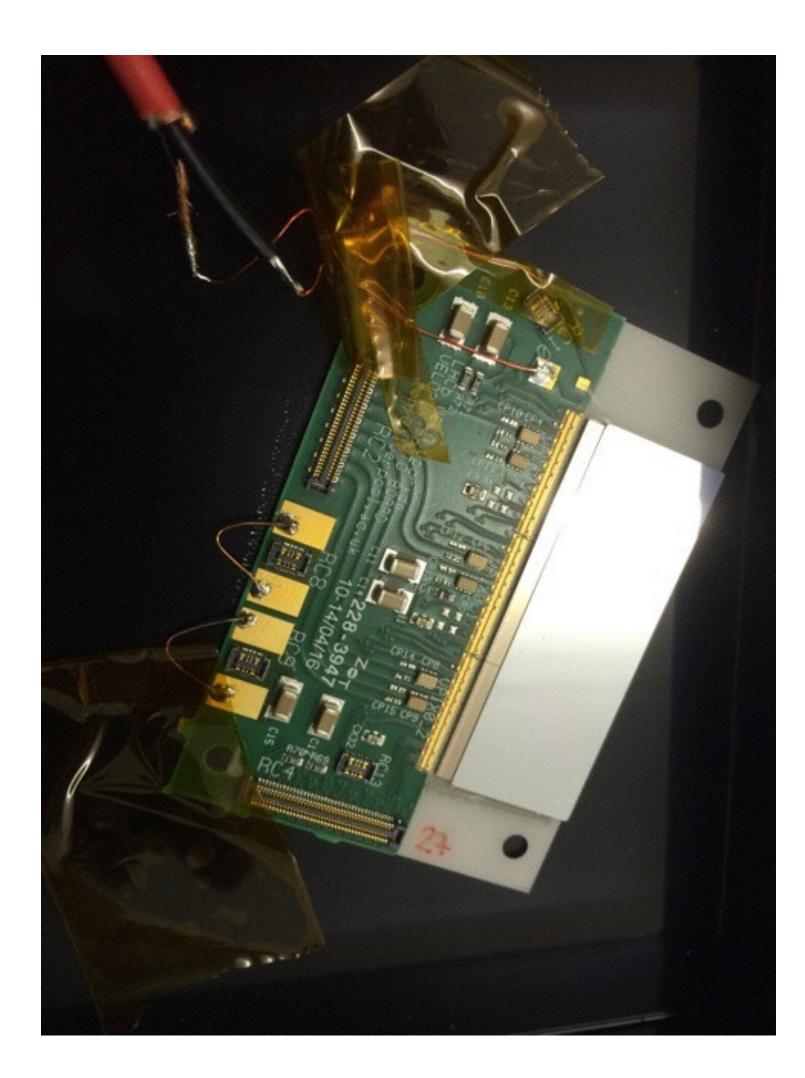


However, even at same temperature behaviour at very high voltages changes.





HPK n-on-p Respin





Variation on original n-on-p design

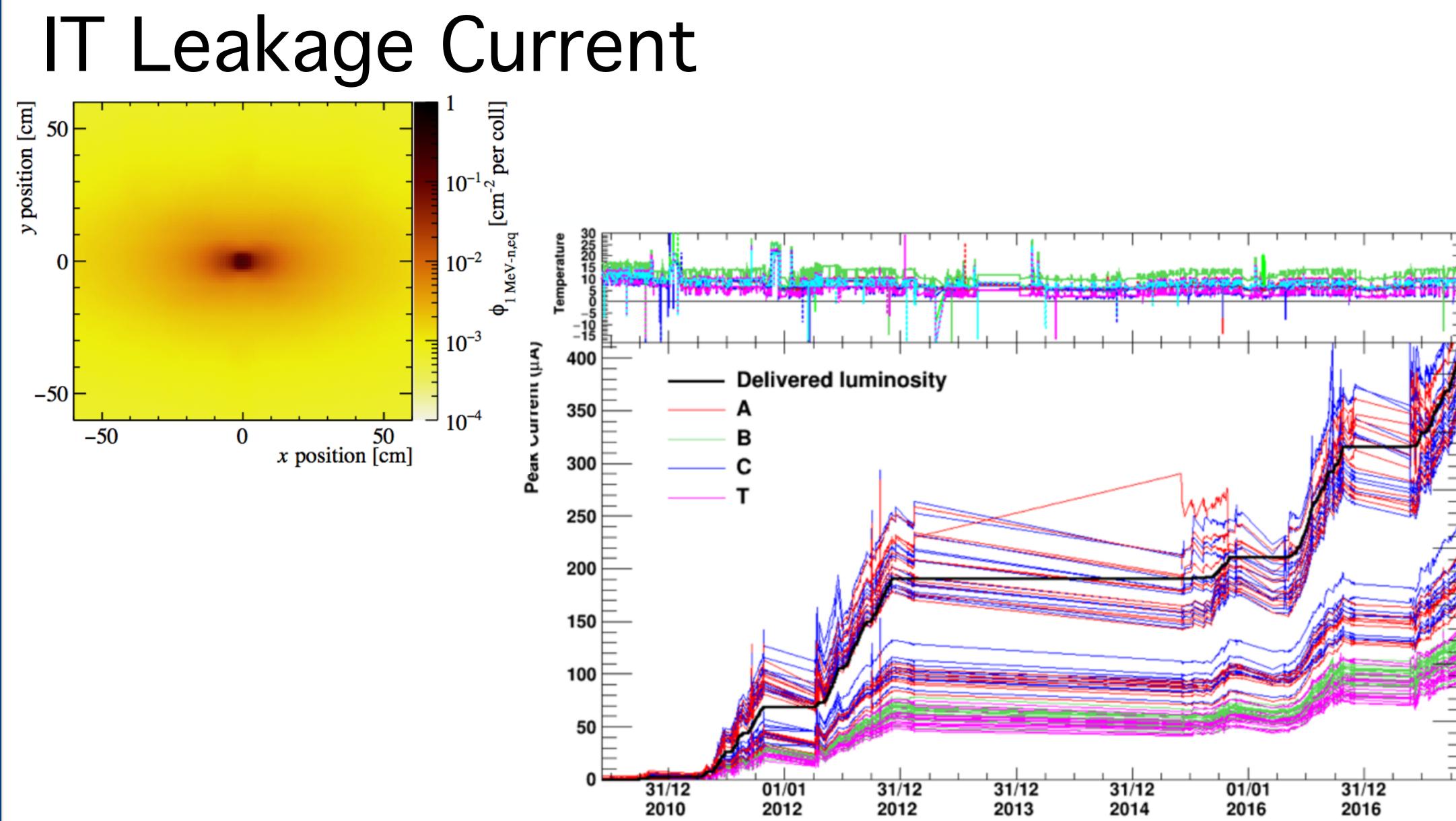
Rounded corners

Longer Interchip distance

Results very fresh















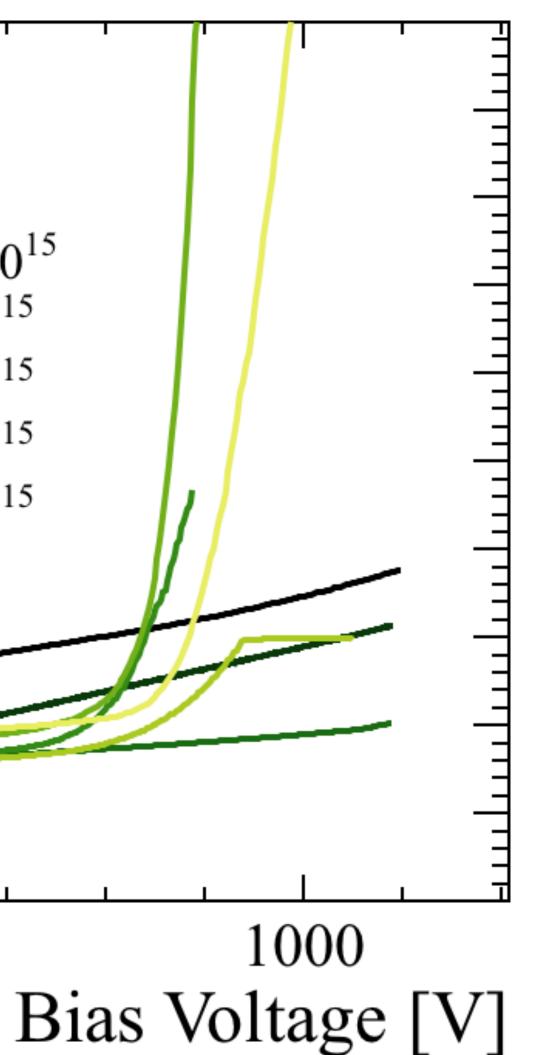
Comparison

0

- S4 Uniform 8×10¹⁵
- S16 Non Uniform 1.14×10¹⁵
- T7 Non Uniform 2.39×10¹⁵
- T2 Non Uniform 1.19×10^{15}
- -- T6 Non Uniform 1.19×10¹⁵

500





All Scaled to -20°C.

Absolute values are very similar, although some features seem slightly different.

Scaling between different irradiations seem to hold well.









Lab Setup

Sensors readout with Timepix3 chip Vacuum and Dry Air operation

